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drawings for purposes of publication, a corrected Figure 2 is attached to this Preliminary Amendment in anticipation of the Examiner's approval of same. It is respectfully requested that once this drawing correction is approved, that the new Figure 2 be entered as soon as possible so as to ensure publication of the revised material.

*and A*  
If, however, the Examiner believes that there are any unresolved issues, it is requested that the Examiner telephone Joseph Pagnotta at (732) 530-9404 so that appropriate arrangements can be made for resolving such issues as expeditiously as possible.

*October 17, 2001*

Respectfully submitted,

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CERTIFICATE OF MAILING under 37 C.F.R. 1.8(a)

I hereby certify that this correspondence is being deposited on October 23, 2001  
with the United States Postal Service as first class mail, with  
sufficient postage, in an envelope addressed to the Assistant Commissioner for  
Patents, Washington, D.C. 20231.

Kenneth Zhran  
Signature

10-23-01  
Date of signature

**APPENDIX**  
**MARK-UP OF AMENDED SPECIFICATION**

**[0019]** In the embodiment shown in FIG. 2, the chamber 202 comprises an antenna 226 adjacent to the chamber that generates an induction coupled field in the chamber to form a high density inductive plasma therein. The inductor antenna 226 preferably comprises multiple coils 226a and 226b positioned adjacent to a chamber ceiling 228 for inductively coupling RF power into the chamber 202. A primary bias electrode 230 comprises a first conducting surface 232 exposed to the plasma zone 206. A unitary monolithic dielectric member 234 positioned directly below the primary bias electrode 230 has a receiving surface 236 for receiving a substrate 118 thereon. A power electrode 238 is embedded in the dielectric member 234. The chamber 202 further comprises a secondary bias electrode 240 positioned directly below the dielectric member 234 and preferably having a second conducting surface 242 exposed to the plasma zone 206. An electrode voltage supply 244 is provided for maintaining the power electrode 238, and the primary and secondary bias electrodes 230, 240 at different electrical potentials relative to one another. Preferably, the power electrode 238 is used to carry both a DC chucking voltage and the RF bias voltage. The voltage supply 244 includes an AC voltage supply for providing a plasma generating RF voltage to the power electrode 238, and a DC voltage supply for providing a chucking voltage to the electrode 238. A separate DC voltage is applied to the electrode 238 to form an electrostatic charge that holds the substrate to the chuck. The RF power is coupled to a bridge circuit and a DC converter to provide DC chucking power to the electrode. The voltage supply [220]244 can also include a system controller for controlling the operation of the electrode by directing a DC current, and RF current, or both, to the electrode for chucking and dechucking the substrate 118 and for generating plasma in the process chamber 202.

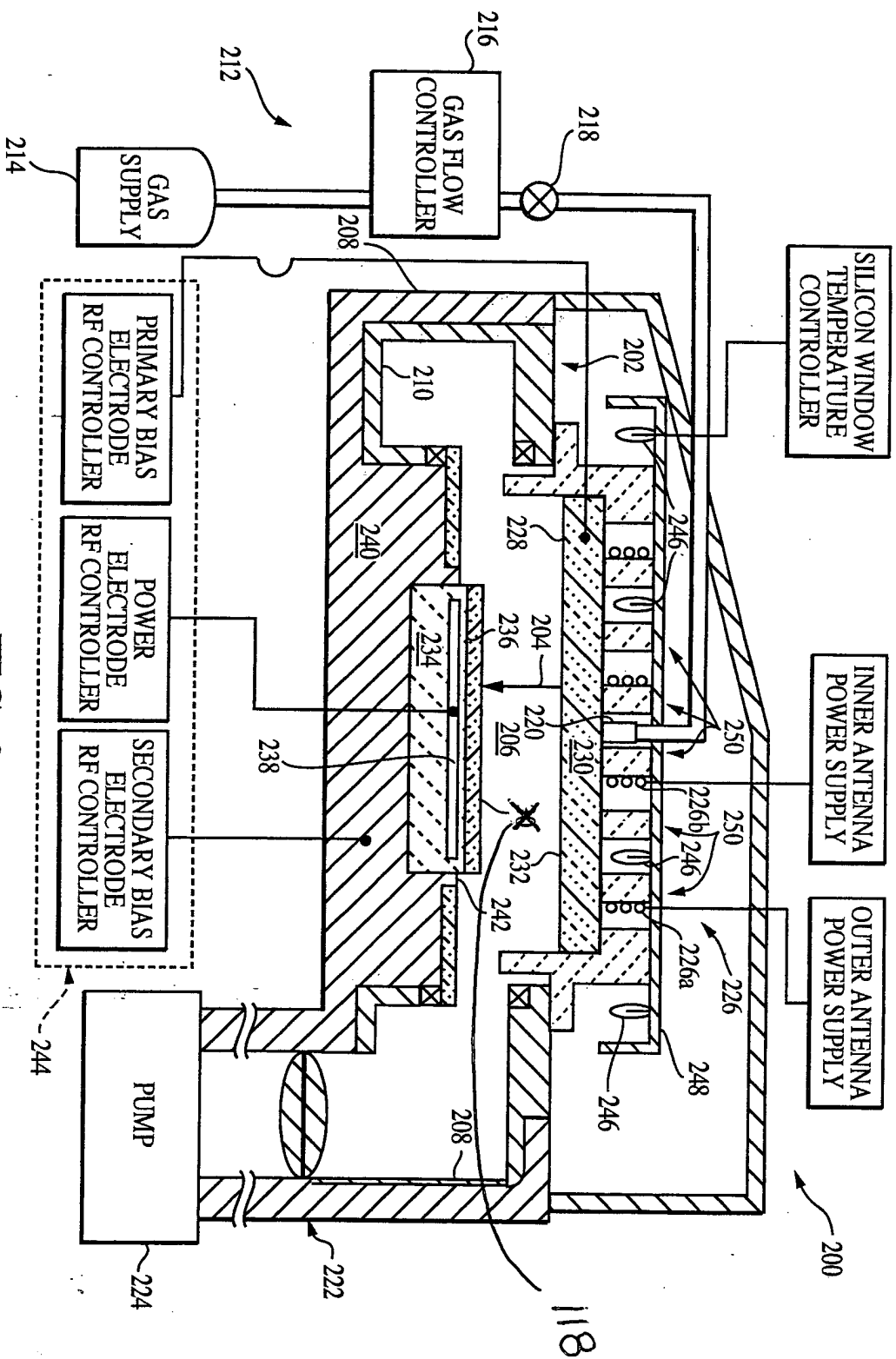


FIG. 2